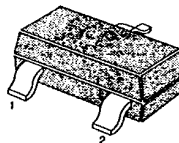


MMBT4126**PNP EPITAXIAL SILICON TRANSISTOR****GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-25	V
Collector-Emitter Voltage	V_{CE0}	-25	V
Emitter-Base Voltage	V_{EB0}	-4	V
Collector Current	I_C	-200	mA
Collector Dissipation	P_C	350	mW
Storage Temperature	T_{stg}	150	$^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{th(j-a)}$	357	$^\circ\text{C/W}$

SOT-23



1. Base 2. Emitter 3. Collector

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV_{CB0}	$I_C = -10\mu\text{A}$, $I_E = 0$	-25		V
*Collector-Emitter Breakdown Voltage	BV_{CE0}	$I_C = -1\text{mA}$, $I_E = 0$	-25		V
Emitter-Base Breakdown Voltage	BV_{EB0}	$I_E = -10\mu\text{A}$, $I_C = 0$	-4		V
Collector Cutoff Current	I_{CBO}	$V_{CB} = -20\text{V}$, $I_E = 0$		-50	nA
Emitter Cutoff Current	I_{EBO}	$V_{BE} = -3\text{V}$, $I_C = 0$		-50	nA
*DC Current Gain	h_{FE}	$V_{CE} = -1\text{V}$, $I_C = -2\text{mA}$	120	360	
		$V_{CE} = -1\text{V}$, $I_C = -50\text{mA}$	60		
*Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}$, $I_B = -5\text{mA}$		-0.4	V
*Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -50\text{mA}$, $I_B = -5\text{mA}$		-0.95	V
Current Gain-Bandwidth Product	f_T	$V_{CE} = -20\text{V}$, $I_C = -10\text{mA}$, $f = 100\text{MHz}$	250		MHz
Collector Input Capacitance	C_{ib}	$V_{BE} = -0.5\text{V}$, $I_C = 0$, $f = 1\text{MHz}$		10	pF
Collector-Base Capacitance	C_{cb}	$V_{CB} = -5\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		4.5	pF
Noise Figure	NF	$V_{CE} = -5\text{V}$, $I_C = -100\mu\text{A}$, $R_s = 1\text{k}\Omega$ Noise Bandwidth = 10Hz to 15.7KHz		4	dB

* Pulse Test: $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Marking

